



AL1698K

### HIGH EFFICIENCY DIMMABLE LED DRIVER

### Description

The DIODES<sup>™</sup> AL1698K is a high efficiency, high performance, high power factor, and high current precision boost, buck-boost, and flyback dimmable LED driver for triac dimmable LED lamp applications. The AL1698K provides an accurate output current over wide line and load regulation. The AL1698K can achieve higher than 90% efficiency by using a boost topology to meet the latest lighting regulatory high efficiency requirements. The wide switching frequency operates at Boundary Conduction Mode (BCM) to ease EMI/EMC design and testing.

The AL1698K LED driver has a built-in high voltage JFET, which provides the system with fast start-up time and enables users an easy and stable VCC supply design. The AL1698K LED driver integrates a 600V/2A high voltage MOSFET. It can cover both  $120V_{AC}$  and  $230V_{AC}$  triac dimmable applications with eliminating the external high voltage MOSFET, which will reduce the system BOM cost. The AL1698K has the built-in thermal fold-back protection trigger point to automatically reduce output current. Other protection features enhance LED lighting system's safety and reliability.

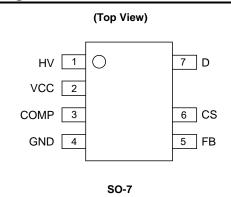
The AL1698K dimming curve is compliant with the NEMA SSL6 standard. The AL1698K applies to a wide range of dimmers, including leading edge and trailing edge dimmer, to achieve deep dimming down to 1%.

The AL1698K is available in SO-7 package.

### Features

- High Efficiency > 90% (Boost Topology)
- Tight Current Sense Tolerance: ± 3%
- Low Operation Current: 310µA
- Single Winding Inductor
- Wide Range of Dimmer Compatibility
- Integration of 600V/2A MOSFET
- Integration of HV JFET
- NEMA SSL6 Dimming Curve Compliant
- Internal Protections
  - Under Voltage Lockout (UVLO)
  - Leading-Edge Blanking (LEB)
  - Cycle-By-Cycle Over Current Protection (OCP)
  - Over Voltage Protection (OVP)
  - Output Short Protection (OSP)
  - Thermal Foldback Protection (TFP)
  - Over Temperature Protection (OTP)
- SO-7 Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>
- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
    - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

# Pin Assignments

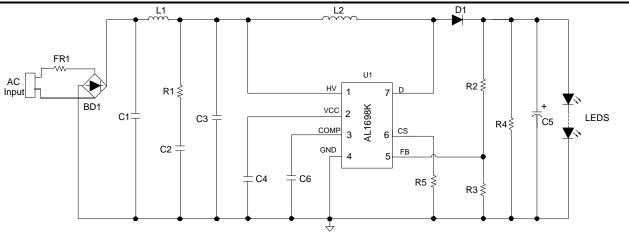


### Applications

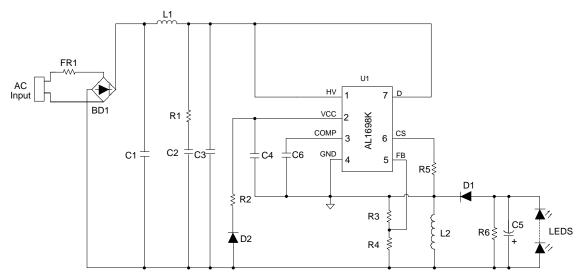
- Mains dimmable LED lamps
- Offline LED power supply drivers



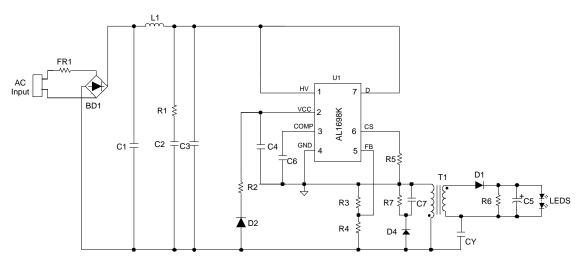
# **Typical Application Circuits**



AL1698K Boost Application Circuit



AL1698K Buck-Boost Application Circuit



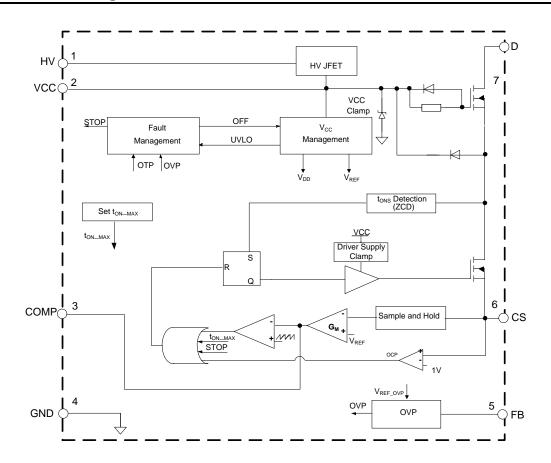
AL1698K Flyback Application Circuit



# **Pin Descriptions**

Pin Number	Pin Name	Function	
1	HV	High Voltage Input Pin	
2	VCC	Power Supply Voltage	
3	COMP	Compensation for Current Control	
4	GND	Ground	
5	FB	Feedback for LED Open Protection Voltage	
6	CS	Current Sensing	
7	D	Drain of the Internal High Voltage MOSFET	

# **Functional Block Diagram**



AL1698K Block Diagram



### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 4)

Symbol	Parameter	Rating	Unit
Vcc	Power Supply Voltage	18	V
VD	Voltage on D Pin	600	V
VHV	Voltage on HV Pin	600	V
IDS	Continuous Drain Current $T_C = +25^{\circ}C$	2	А
Vcs	Voltage on CS Pin	-0.3 to 7	V
Vfb	Voltage on FB Pin	-0.3 to 7	V
TJ	Operating Junction Temperature	-40 to +150	°C
Тѕтс	Storage Temperature	-65 to +150	°C
TLEAD	Lead Temperature (Soldering, 10s)	+260	°C
PD	Power Dissipation ( $T_A = +50^{\circ}C$ ) (Note 5)	0.8	W
θја	Thermal Resistance (Junction to Ambient) (Note 5)	115	°C/W
θις	Thermal Resistance (Junction to Case) (Note 5)	19	°C/W
	ESD (Human Body Model) (Note 6)	2,000	V
—	ESD (Charged-Device Model)	1,000	V

Notes: 4. Stresses greater than those listed under "Absolute Maximum Ratings" can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods can affect device reliability. All voltages unless otherwise stated and measured with respect to GND.

5. Device mounted on 1"x1" FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.

6. All other pins pass 2000V except for Pin1. Pin1 passes 1000V.

# Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Мах	Unit
TA	Ambient Temperature (Note 7)	-40	+105	°C
V <sub>CC</sub>	Operating V <sub>CC</sub> Voltage	7.3	V <sub>CC_CLAMP</sub> (Min)	V
V <sub>DS</sub>	Drain-Source Breakdown Voltage		500	V

Note: 7. The device may operate normally at +125°C ambient temperature under the condition not trigger temperature protection.



### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

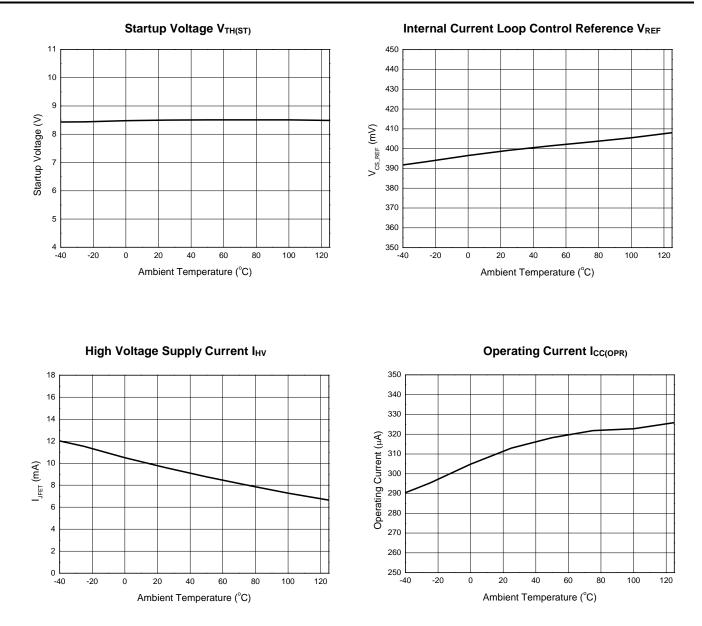
Symbol	Parameter	Condition	Min	Тур	Max	Unit
UVLO						
VTH(ST)	Startup Voltage —		7	8.8	10	V
VOPR(MIN)	Minimum Operating Voltage	After Turn On	5.5	7.1	8.5	V
Vcc_clamp	V <sub>CC</sub> Clamp Voltage	lcc = 1mA	7.5	9.5	10.5	V
Vcc_charge	Vcc UVLO	—	3.5	4.2	5.5	V
Standby Current						
I <sub>CC(OPR)</sub>	Operating Current	Switching Frequency at 3kHz	_	310	—	μA
High Voltage Startup Cu	urrent Source				•	
Іну	High Voltage Supply Current	$V_{CC} = V_{TH(ST)} - 1.5V,$ $V_{D} = 40V$	7	10.5	_	mA
ILEAK	Leakage Current of Drain	$V_{CC} = V_{TH(ST)} + 0.5V,$ $V_{D} = 500V$	_	5	—	μA
Source Driver						
Rds(on)_LV	Internal Low Voltage MOSFET On-State Resistance (Note 8)	—	_	1	—	Ω
High Voltage MOSFET						
Rds(on)_hv	Static Drain-Source On-State Resistance	_	—	4.7	5.5	Ω
V <sub>DS</sub>	Drain-Source Breakdown Voltage	(Note 9)	600	-	—	V
Current Sense						
Vcs_clamp	Current Sense Clamp Voltage	—	1.1	1.2	1.3	V
VREF	Internal Current Loop Control Reference	_	0.388	0.4	0.412	V
ton_min	Minimum ton	—	—	610	—	ns
ton_max	Maximum toN	VCOMP = 4V	—	10	—	μs
toff_min	Minimum toff (Note 8)	_	—	4		μs
toff_max	Maximum toff	—	—	313		μs
FB Pin					-	-
V <sub>FB</sub>	Feedback Voltage	—	1.88	2	2.12	V
Error Amplifier						
GM	G <sub>M</sub> Trans-Conductance	—	_	25	_	μA/V
ISOURCE	Amplifier Source Current	Vcs = 0V	_	10	—	μA
Isink	Amplifier Sink Current	Vcs = 1V	_	15	_	μA
Thermal Foldback and (	Over Temperature Protection (OTP)					
T <sub>FOLD</sub>	Thermal Foldback (Note 8)	_	_	+150	—	°C
_	Thermal Shutdown (Notes 8 and 10)	_	_	+170		°C

Notes:

8. These parameters, although guaranteed by design, are not tested in production.
 9. The drain-source voltage is 80% of V<sub>DS</sub> in the aging condition.
 10. The device will latch off when OTP happens, recovered after power cycle and the device won't operate normally at this temperature.



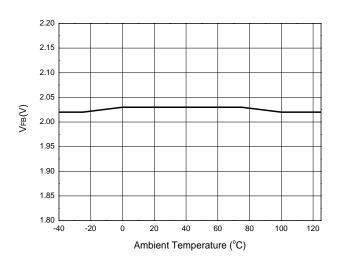
### Performance Characteristics (Note 11)



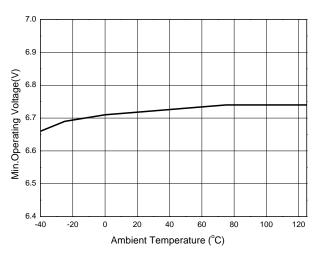
Note: 11. These electrical characteristics are tested under DC condition. The ambient temperature is equal to the junction temperature of the device.



### Performance Characteristics (continued) (Note 11)



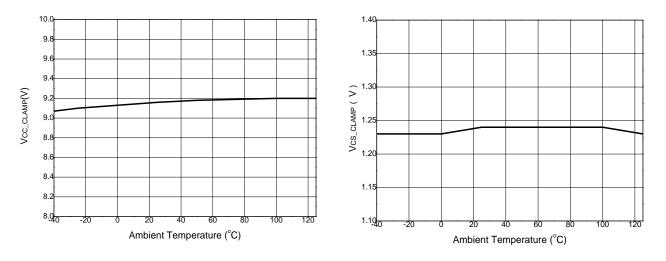
### Feedback Voltage VFB



#### Minimum Operating Voltage VOPR(MIN)



Current Sense Clamp Voltage Vcs\_clamp



Note: 11. These electrical characteristics are tested under DC condition. The ambient temperature is equal to the junction temperature of the device.



### **Functional Description and Application Information**

#### Operation

The AL1698K is a single stage, single winding, high efficiency, and high power factor dimmable LED driver for triac dimmable LED lamp applications. The AL1698K integrates a high voltage JFET and a 600V/2A high voltage MOSFET, and it can cover 230V<sub>AC</sub> triac dimmable applications with eliminating external high voltage MOSFET and V<sub>CC</sub> startup resistors.

The AL1698K adopts source-driver technique to decrease the system operating current. It uses a novel method to detect the toFF time which results in the removal for the need of an auxiliary winding. The AL1698K operates at Boundary Conduction Mode (BCM) which can ease EMI design and achieve high efficiency. High Power Factor (HPF) is achieved by using constant on-time mode. Coupled with a closed loop of constant current control, the AL1698K achieves good line and load regulation.

#### Startup and Supply Voltage

Before startup, the VCC capacitor C4 is charged by internal HV JFET. When the start-up voltage is reached, the AL1698K starts switching.

The AL1698K has an internal Vcc clamp voltage (typical 9.5V), which is limited by one internal active Zener diode.

When V<sub>CC</sub> voltage drops to below the V<sub>OPR(MIN)</sub>, switching will be stopped. So the device can operate normally when the voltage on VCC pin is between V<sub>OPR(MIN)</sub> and V<sub>CC</sub> clamp voltage.

#### Protections

#### Under Voltage Lockout (UVLO)

When the voltage on the VCC pin drops below V<sub>CC\_CHARGE</sub>, the IC stops switch. The IC can restart when the voltage on VCC exceeds the startup voltage (V<sub>TH(ST)</sub>).

#### Leading-Edge Blanking (LEB)

To prevent false detection of the peak current of the inductor, a blanking time following switch-on is designed. When the internal switch turns on, a short current spike can occur because of the capacitive discharge of the voltages over the drain and source. It is disregarded during the LEB time (ton\_min).

#### Cycle-by-Cycle Over Current Protection (OCP)

The AL1698K has a built-in peak current detector. It is triggered when the voltage on CS pin reaches the peak level  $V_{CS\_CLAMP}$ . The R5 is connected to the CS pin to sense the current of the inductor. The maximum peak current (IPEAK(MAX)) of the inductor can be calculated as below:

$$I_{PEAK(MAX)} = \frac{V_{CS\_CLAMP}}{R5}$$

The detection circuit is activated after the LEB time. When the detection circuit senses the CS voltage higher than 1V, the IC will turn off the switching to limit the output current. It automatically provides protection for the maximum LED current during operation. A propagation delay exists between over current detection and actual source-switch off, so the actual peak current is a little higher than the OCP level set by the R5.

#### Over Voltage Protection (OVP) and Output Open Protection

The output voltage is sensed by the FB pin, which provides an over-voltage protection (OVP) function. When the output is open or large transient happens, the output voltage will exceed the rated value (R4, R3). When the voltage exceeds  $V_{FB}$ , the over-voltage is triggered and the IC will discharge  $V_{CC}$ . When the  $V_{CC}$  is below the UVLO threshold voltage, IC will restart and the  $V_{CC}$  capacitor is charged again by start-up resistance. If the over voltage condition still exists, the system will work in hiccup mode.

#### **Output-Short Protection (OSP)**

When LED is shorted, the device cannot detect the toFF time, and the device controls the system operation at 4kHz low frequency.

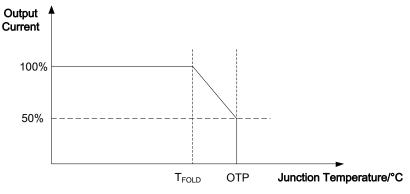


### Functional Description and Application Information (continued)

#### Thermal Foldback Protection (TFP)

AL1698K has a Thermal Foldback Protection (TFP) function and adopts self-adaptive control method, which can prevent the system breaking down caused by high temperature. The overheating temperature is set at +150°C typical. When the junction temperature of the IC is higher than +150°C typical, the device will linearly decrease the internal reference voltage to decrease the output current. As a result of this feature, the device can control the system's output power at high ambient temperature, to control the system heat quality. This enhances the safety of the system at high temperature.

Thermal foldback waveform is shown below.





#### **Over-Temperature Protection (OTP)**

The AL1698K has Over Temperature Protection (OTP) function. When the junction temperature reaches +170°C typical, the IC will trigger an overtemperature protection, which causes the device to shut down and latch up. Once OTP is triggered, the system needs to be resumed after the system's AC source supply has been reset and powered up.

#### **Design Parameters**

#### Setting the Current Sense Resistor R5

The AL1698K adopts Boundary Conduction Mode, the output current is calculated as below:

$$I_{O\_MEAN} = \frac{1}{\pi} \cdot \int_{0}^{\pi} \frac{1}{2} \cdot I_{PEAK} \cdot \frac{t_{OFF}}{t_{ON} + t_{OFF} + t_{DELAY}} dt \qquad (2)$$

Where,

 $\label{eq:IPEAK} I_{PEAK} is the peak current of the inductance. to N is the internal MOSFET on time. to FF is the freewheel diode D1 conduction time. tdelay is typical 0.4 \mu s.$ 

The AL1698K is a closed loop constant current control with the relationship between output current and current sense voltage follows this equation:

$$V_{REF} = \frac{1}{\pi} \cdot \int_{0}^{\pi} I_{PEAK} \cdot \mathbf{R5} \cdot \frac{t_{OFF}}{t_{ON} + t_{OFF} + t_{DELAY}} dt$$

Where,

V<sub>REF</sub> is the internal reference, typical 0.4V. R5 is the current sense resistor.

So we can get the output current equation as below:

$$I_{O\_MEAN} = \frac{1}{2} \cdot \frac{V_{REF}}{R5}$$

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### Functional Description and Application Information (continued)

#### Inductance Selection (L2)

In buck-boost structure, the peak current of the inductance can be calculated as below:

$$I_{PEAK} = \frac{\pi \cdot V_{REF}}{R5 \cdot \int_{0}^{\pi} \sin(\theta) \cdot \frac{\sqrt{2} \cdot V_{IN\_RMS} \cdot \sin(\theta)}{\sqrt{2} \cdot V_{IN\_RMS} \cdot \sin(\theta) + Vo} d\theta}$$

Where,

VIN\_RMS is the input voltage's RMS value.

Vo is the system output voltage.

The AL1698K controls the system operating at Boundary Conduction Mode which results in its operating frequency not being constant. To set the minimum switching frequency f<sub>MIN</sub> at the crest of the minimum AC input:

 $L2 = \frac{\sqrt{2}V_{IN\_RMS} \cdot V_O}{I_{PEAK} \cdot (\sqrt{2}V_{IN\_RMS} + V_O) \cdot f_{MIN}}$ 

According to the Faraday's Law, the winding number of the inductance can be calculated by:

$$N_{L2} = \frac{L2 \cdot I_{PEAK}}{A_e \cdot B_m} \tag{7}$$

Where,

Ae is the core effective area.

 $B_m$  is the maximum magnetic flux density.

#### **Dimming Control**

The AL1698K is a closed loop control device; the dimming function is realized by toN\_MAX limited when dimmer is connected in. When the dimmer is at the largest conduction angle, the device still has the adjustability to control the output current constant before COMP voltage is adjusted to the maximum 4V, so for most of the dimmer, the output current is almost the same with the no dimmer condition at the largest conduction angle. If the conduction angle is decreased, the COMP pin voltage will continue to increase quickly till to the maximum level (typical 4V), the device will output toN\_MAX to limit system's output current. The toN\_MAX is set by RT pin connected with one resistor, so the dimming depth can be adjusted by RT resistor (R6).

Before the AL1698K enters ton\_MAX mode, it keeps the output current constant the same as no dimmer condition. When enter ton\_MAX mode, we can get the following equation:

$$I_{PEAK\_DIM} = \frac{V_{IN\_RMS} \cdot Sin(\theta) \cdot t_{ON\_MAX}}{L2}$$
(8)

From the buck-boost output current equation, we can get the output current when dimming:

$$I_{o}(\theta) = \begin{cases} \frac{1}{2} \cdot \frac{V_{REF}}{R5} & \text{if } t_{oN} < t_{oN\_MAX} \\ \frac{1}{\pi} \int_{0}^{\alpha} \frac{1}{2} \cdot I_{PEAK\_DIM} \cdot \frac{\sqrt{2}V_{IN\_RMS} \cdot Sin(\theta)}{\sqrt{2}V_{IN\_RMS} \cdot Sin(\theta) + V_{o}} d\theta & \text{else} \end{cases}$$

Where,

 $\alpha$  is the dimmer conduction angle.

..... (9)



### Functional Description and Application Information (continued)

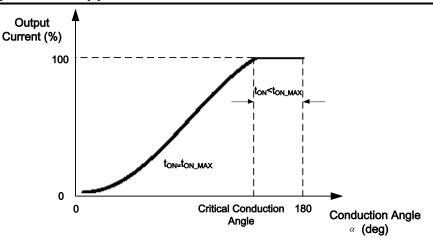


Figure 2. Dimming Curve

#### **Dimmer Compatibility**

#### **Passive Bleeder Design**

The passive bleeder is designed to supply latching and holding current to eliminate dimmer misfire and flicker.

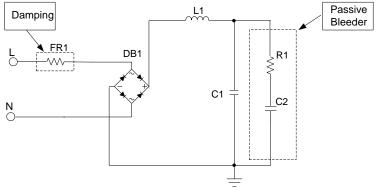


Figure 3. LED Driver Schematic with Passive Bleeder

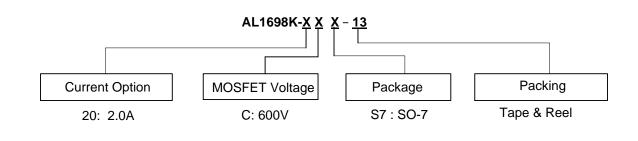
The passive bleeder includes a capacitor (C2, in hundreds of nF) to provide latching current. A resistor (R1) is necessary to dampen the current spike. Because a large C2 will affect the PF, THD and efficiency, the value of the capacitor (C2) should be selected accordingly. Generally, 100nF/400V to 330nF/400V is recommended. R1 is used to limit the latching current. If R1 is too large, the latching current is not enough and the triac dimmer will misfire causing LED flicker. If R1 is too small, it will result in greater power dissipation. Generally speaking, a  $200\Omega$  to  $2k\Omega$  resistor is selected for R1.

#### Passive Damping Design

FR1 is the damper for reducing the spike current caused by quick charging of C2 at firing. In general, FR1 is selected from  $20\Omega$  to  $100\Omega$  for low line like  $120V_{AC}$  application, and  $51\Omega$  to  $200\Omega$  for high line like  $230V_{AC}$  application.

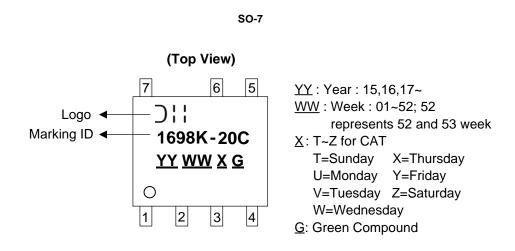


### **Ordering Information**



Don't Number	Baakawa Cada	Deckere	Marking ID	Packing		
Part Number	Package Code	Package		Qty.	Carrier	
AL1698K-20CS7-13	S7	SO-7	1698K-20C	4,000	13" Tape & Reel	

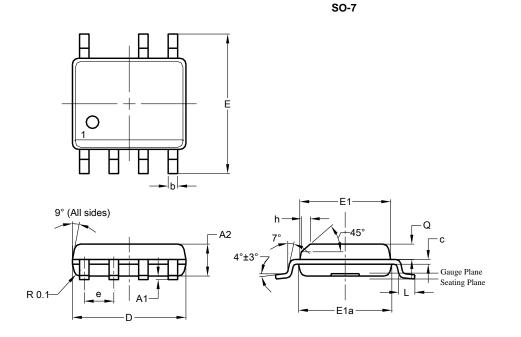
# **Marking Information**





## **Package Outline Dimensions**

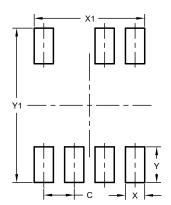
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-7					
Dim					
A2	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
E	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E1a	3.85	3.95	3.90		
е	-	-	1.27		
h	-	-	0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.270
Х	0.802
X1	4.612
Y	1.505
Y1	6.500

### **Mechanical Data**

- Moisture Sensitivity: Level 1 per JESD22-A113
- Terminals: Finish Matte Tin Plated Leads, Solderable per M2003 JESD22-B102 (3)
- Weight: 0.077 grams (Approximate)

SO-7



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